8M-Bit (1Mx8) CMOS MASK ROM

FEATURES

- 1,048,576 x 8 bit organization
- Fast access time : 100ns(Max.)
- Supply voltage : single +5V
- Current consumption
  Operating : 50mA(Max.)
  Standby : 50μA(Max.)
- Fully static operation
- All inputs and outputs TTL compatible
- Three state outputs
- Package
  -. K3N4C3000D-DC : 32-DIP-600
  -. K3N4C3000D-GC : 32-SOP-525

GENERAL DESCRIPTION

The K3N4C3000D-D(G)C is a fully static mask programmable ROM organized 1,048,576 x 8 bit. It is fabricated using silicon gate CMOS process technology.

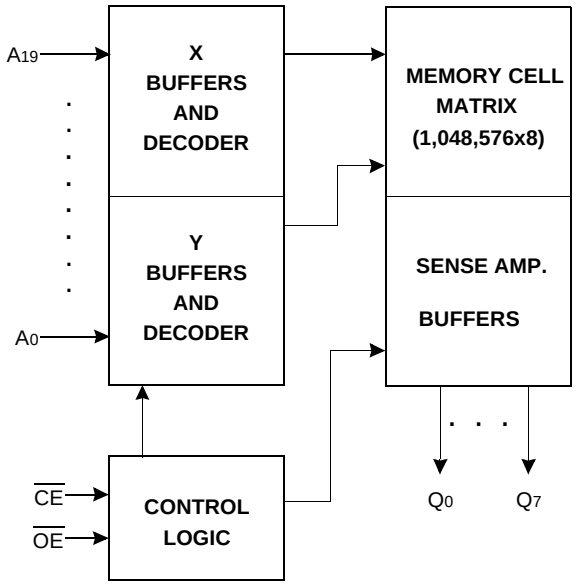
This device operates with a 5V single power supply, and all inputs and outputs are TTL compatible.

Because of its asynchronous operation, it requires no external clock assuring extremely easy operation.

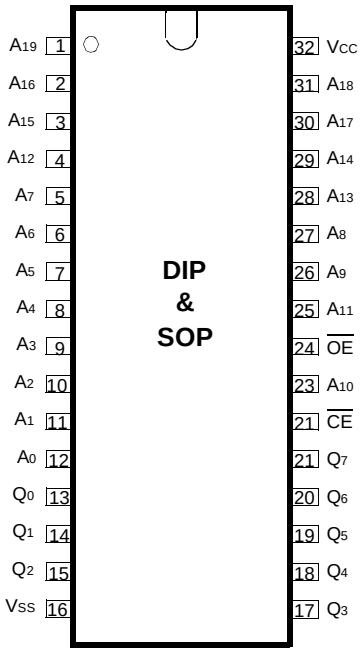
It is suitable for use in program memory of microprocessor, and data memory, character generator.

The K3N4C3000D-DC is packaged in a 32-DIP and the K3N4C3D-GC in a 32-SOP.

FUNCTIONAL BLOCK DIAGRAM



PIN CONFIGURATION



K3N4C3000D-D(G)C

Pin Name	Pin Function
A_0 - A_{19}	Address Inputs
Q_0 - Q_7	Data Outputs
$\overline{CE}$	Chip Enable
$\overline{OE}$	Output Enable
V_{CC}	Power (+5V)
V_{SS}	Ground

ABSOLUTE MAXIMUM RATINGS

Item	Symbol	Rating	Unit
Voltage on Any Pin Relative to V_{SS}	V_{IN}	-0.3 to +7.0	V
Temperature Under Bias	T_{BIAS}	-10 to +85	°C
Storage Temperature	T_{STG}	-55 to +150	°C

NOTE : Permanent device damage may occur if "ABSOLUTE MAXIMUM RATINGS" are exceeded. Functional operation should be restricted to the conditions as detailed in the operational sections of this data sheet. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS(Voltage reference to V_{SS}, T_A=0 to 70°C)

Item	Symbol	Min	Typ	Max	Unit
Supply Voltage	V_{CC}	4.5	5.0	5.5	V
Supply Voltage	V_{SS}	0	0	0	V

DC CHARACTERISTICS

Parameter	Symbol	Test Conditions	Min	Max	Unit
Operating Current	I_{CC}	Cycle=5MHz, all outputs open $\overline{CE}$=$\overline{OE}$=V_{IL}, V_{IN}=0.6V to 2.4V (AC Test Condition)	-	50	mA
Standby Current(TTL)	I_{SB1}	$\overline{CE}$=V_{IH}, all outputs open	-	1	mA
Standby Current(CMOS)	I_{SB2}	$\overline{CE}$=V_{CC}, all outputs open	-	50	µA
Input Leakage Current	I_{LI}	V_{IN}=0 to V_{CC}	-	10	µA
Output Leakage Current	I_{LO}	V_{OUT}=0 to V_{CC}	-	10	µA
Input High Voltage, All Inputs	V_{IH}		2.2	V_{CC}+0.3	V
Input Low Voltage, All Inputs	V_{IL}		-0.3	0.8	V
Output High Voltage Level	V_{OH}	I_{OH}=-400µA	2.4	-	V
Output Low Voltage Level	V_{OL}	I_{OL}=2.1mA	-	0.4	V

NOTE : Minimum DC Voltage(V_{IL}) is -0.3V an input pins. During transitions, this level may undershoot to -2.0V for periods <20ns.
Maximum DC voltage on input pins(V_{IH}) is V_{CC}+0.3V which, during transitions, may overshoot to V_{CC}+2.0V for periods <20ns.

MODE SELECTION

$\overline{CE}$	$\overline{OE}$	Mode	Data	Power
H	X	Standby	High-Z	Standby
L	H	Operating	High-Z	Active
	L	Operating	Dout	Active

CAPACITANCE(T_A=25°C, f=1.0MHz)

Item	Symbol	Test Conditions	Min	Max	Unit
Output Capacitance	C_{OUT}	V_{OUT}=0V	-	12	pF
Input Capacitance	C_{IN}	V_{IN}=0V	-	12	pF

NOTE : Capacitance is periodically sampled and not 100% tested.

AC CHARACTERISTICS(T_A=0°C to +70°C, V_{CC}=5.0V±10%, unless otherwise noted.)

TEST CONDITIONS

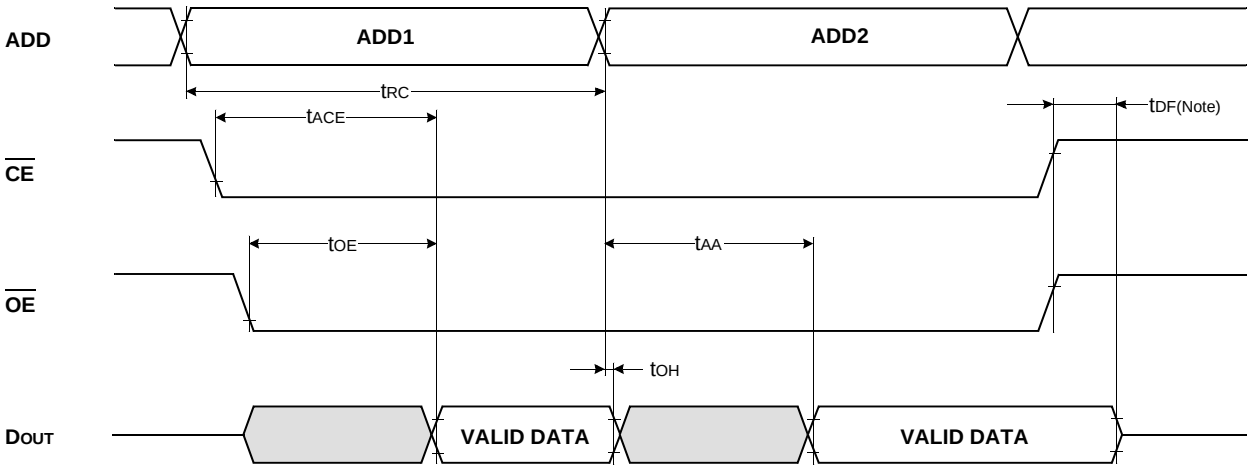
Item	Value
Input Pulse Levels	0.6V to 2.4V
Input Rise and Fall Times	10ns
Input and Output timing Levels	0.8V and 2.0V
Output Loads	1 TTL Gate and C_L=100pF

READ CYCLE

Item	Symbol	K3N4C3000D-D(G)C10		K3N4C3000D-D(G)C12		K3N4C3000D-D(G)C15		Unit
		Min	Max	Min	Max	Min	Max	
Read Cycle Time	t_{RC}	100		120		150		ns
Chip Enable Access Time	t_{ACE}		100		120		150	ns
Address Access Time	t_{AA}		100		120		150	ns
Output Enable Access Time	t_{OE}		50		60		70	ns
Output or Chip Disable to Output High-Z	t_{DF}		20		20		30	ns
Output Hold from Address Change	t_{OH}	0		0		0		ns

TIMING DIAGRAM

READ



NOTE : t_{DF} is defined as the time at which the outputs achieve the open circuit condition and is not referenced to V_{OH} or V_{OL} level.